

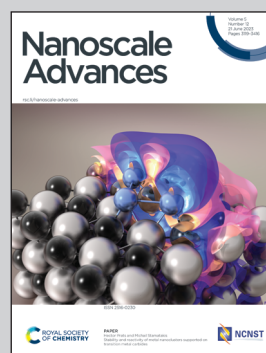


Showcasing research from Dr Abdelkarim Ouerghi's laboratory, CNRS, Centre de Nanosciences et de Nanotechnologies, Université Paris-Saclay, Palaiseau, France.

High p doped and robust band structure in Mg-doped hexagonal boron nitride

Nano-angle-resolved photoemission measurements are used to study the electronic properties of Mg-doped h-BN grown by solidification from a ternary Mg–B–N system. Our findings demonstrate that conventional semiconductor doping by Mg as substitutional impurities is a promising route to high-quality p-type doped h-BN films.

As featured in:



See Abdelkarim Ouerghi *et al.*, *Nanoscale Adv.*, 2023, 5, 3225.